April 2014

FDA8440

N-Channel Logic Level PowerTrench® MOSFET

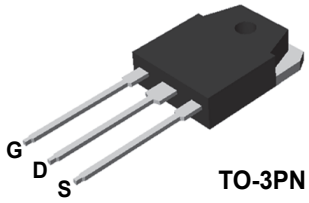
40 V, 100 A, 2.1 mΩ

Features

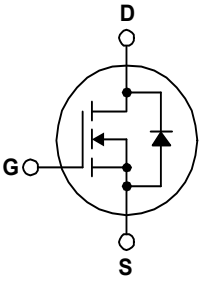
- $R_{DS(on)}$ = 1.46 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 80 A
- $Q_{G(tot)}$ = 345 nC (Typ.) @ V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- 160 A Guarantee for 2 sec
- RoHS Compliant

Application

- Power tools
- Motor drives and Uninterruptible Power Supplies
- Synchronous Rectification
- Battery Protection Circuit



TO-3PN



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDA8440	Unit
V_{DSS}	Drain to Source Voltage		40	V
V_{GSS}	Gate to Source Voltage		±20	V
I_D	Drain Current - Continuous (T_C = 155°C)		100	A
	- Continuous (T_A = 25°C, V_{GS} = 10 V, $R_{\theta JA}$ = 40°C/W)		30	A
	- Pulsed		500	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 1)	1682	mJ
P_D	Power dissipation		306	W
	Derate above 25°C		2.04	W/°C
T_J, T_{STG}	Operating and Storage Temperature		-55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.		0.49	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	(Note 2)	40	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA8440	FDA8440	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions		Min.	Typ.	Max.	Unit
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA		40	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 32 V		--	--	1	μA
		V_{GS} = 0 V	T_C = 150°C	--	--	250	μA
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±20 V		--	--	±100	nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA		1	--	3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 4.5 V, I_D = 80 A		--	1.56	2.2	mΩ
		V_{GS} = 10 V, I_D = 80 A		--	1.46	2.1	
		V_{GS} = 10 V, I_D = 80 A, T_C = 175°C		--	2.82	4.1	
Dynamic Characteristics							
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		--	18600	24740	pF
C_{oss}	Output Capacitance			--	1840	2450	pF
C_{rss}	Reverse Transfer Capacitance			--	1400	2100	pF
R_G	Gate Resistance	V_{GS} = 0.5 V, f = 1 MHz		--	1.1	--	Ω
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{GS} = 0 V to 10 V	V_{DD} = 20 V, I_D = 80 A, I_g = 1.0 mA	--	345	450	nC
$Q_{g(2)}$	Threshold Gate Charge	V_{GS} = 0 V to 2 V		--	32.5	--	nC
Q_{gs}	Gate to Source Gate Charge			--	49	--	nC
Q_{gs2}	Gate Charge Threshold to Plateau			--	16.5	--	nC
Q_{gd}	Gate to Drain “Miller” Charge			--	74	--	nC
Switching Characteristics							
t_{ON}	Turn-On Time	V_{DD} = 20 V, I_D = 80 A, V_{GS} = 10 V, R_{GEN} = 7 Ω		--	175	360	ns
$t_{d(on)}$	Turn-On Delay Time			--	43	95	ns
t_r	Rise Time			--	130	275	ns
$t_{d(off)}$	Turn-Off Delay Time			--	435	875	ns
t_f	Fall Time			--	290	590	ns
t_{OFF}	Turn-Off Time			--	730	1470	ns
Drain-Source Diode Characteristics and Maximum Ratings							
V_{SD}	Source to Drain Diode Voltage	I_{SD} = 80 A		--	--	1.25	V
		I_{SD} = 40 A		--	--	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD} = 75 A, dI_{SD}/dt = 100 A/μs		--	59	--	ns
Q_{RR}	Reverse Recovery Charge	I_{SD} = 75 A, dI_{SD}/dt = 100 A/μs		--	77	--	nC

NOTES:

1: Starting T_J = 25°C, L = 1 mH, I_{AS} = 58 A, V_{DD} = 36 V, V_{GS} = 10 V.

2: Pulse width = 100 s.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

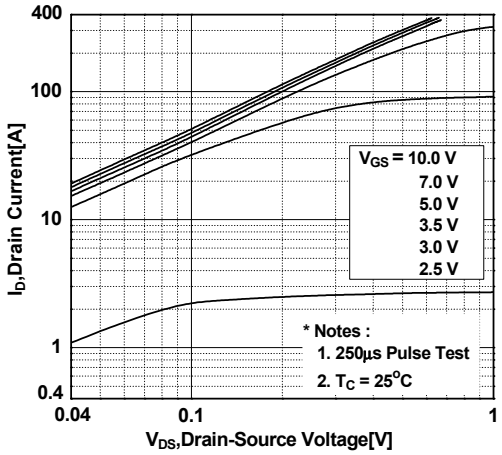


Figure 2. Transfer Characteristics

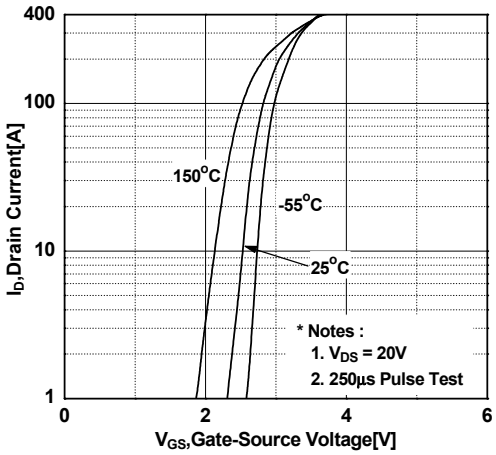


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

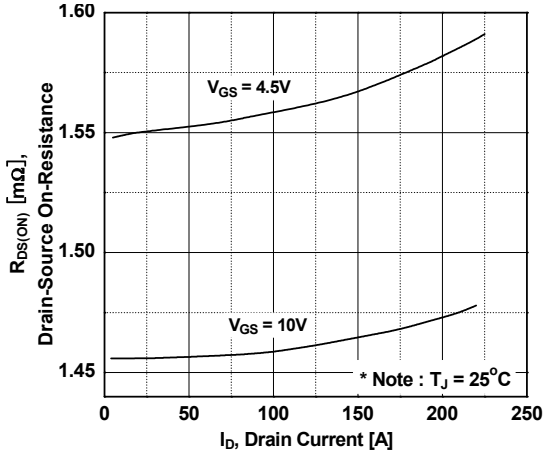


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

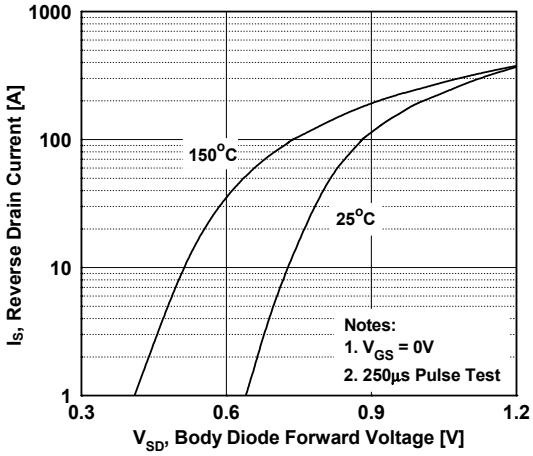


Figure 5. Capacitance Characteristics

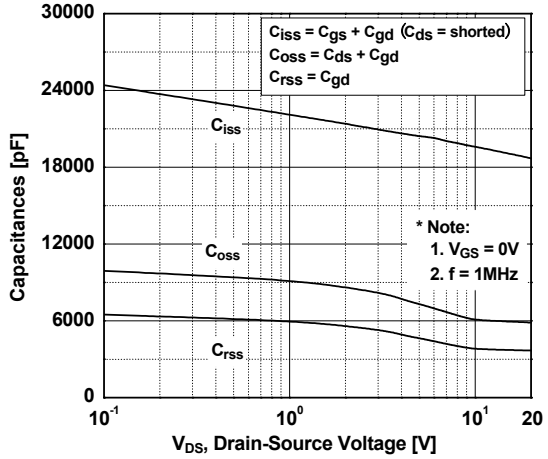
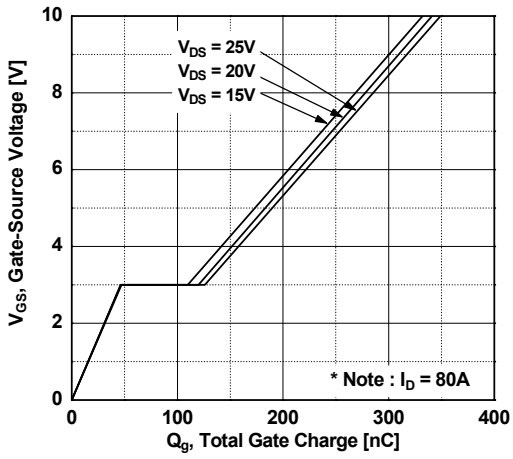


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

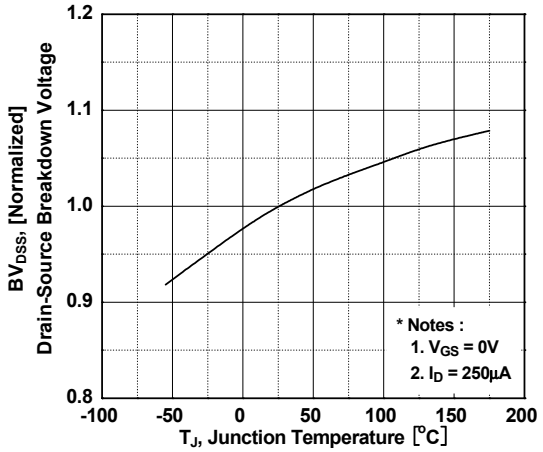


Figure 8. On-Resistance Variation vs. Temperature

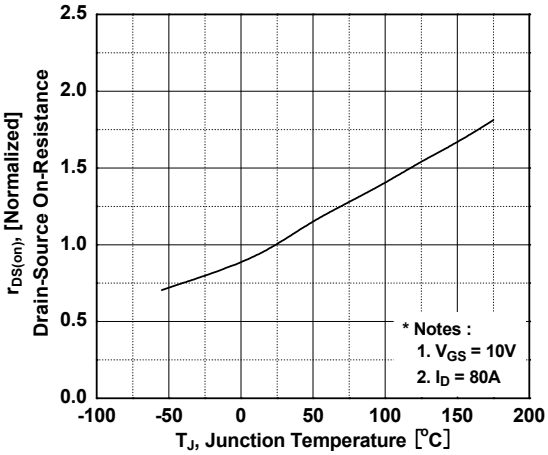


Figure 9. Unclamped Inductive Switching Capability

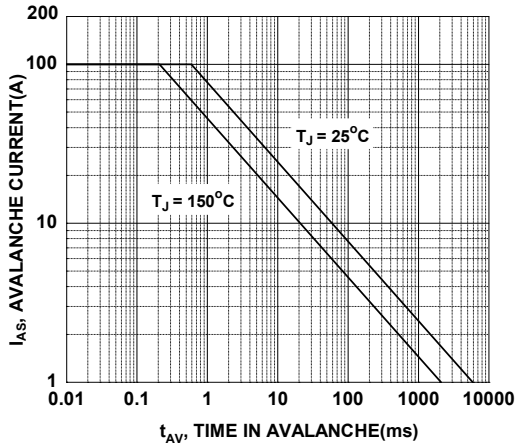


Figure 10. Safe Operating Area

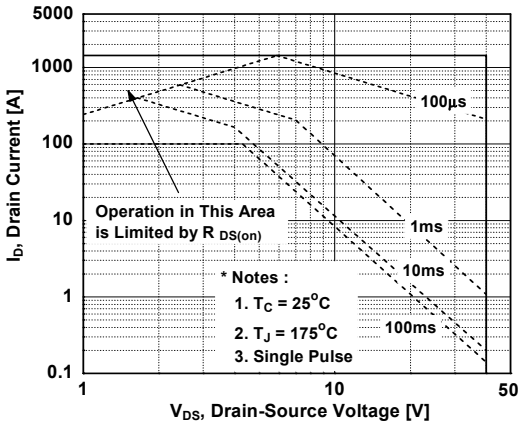
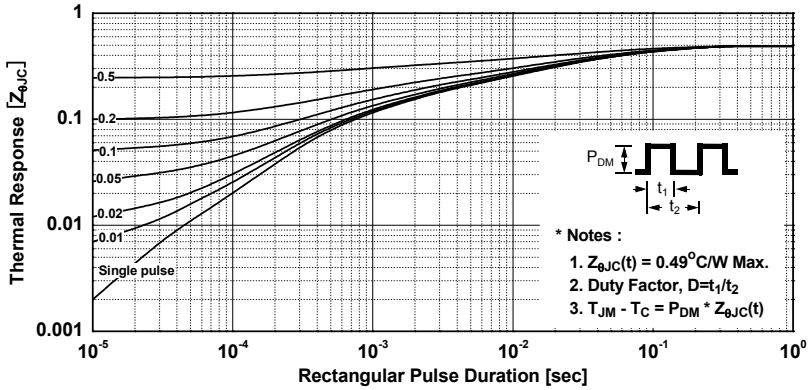


Figure 11. Transient Thermal Response Curve



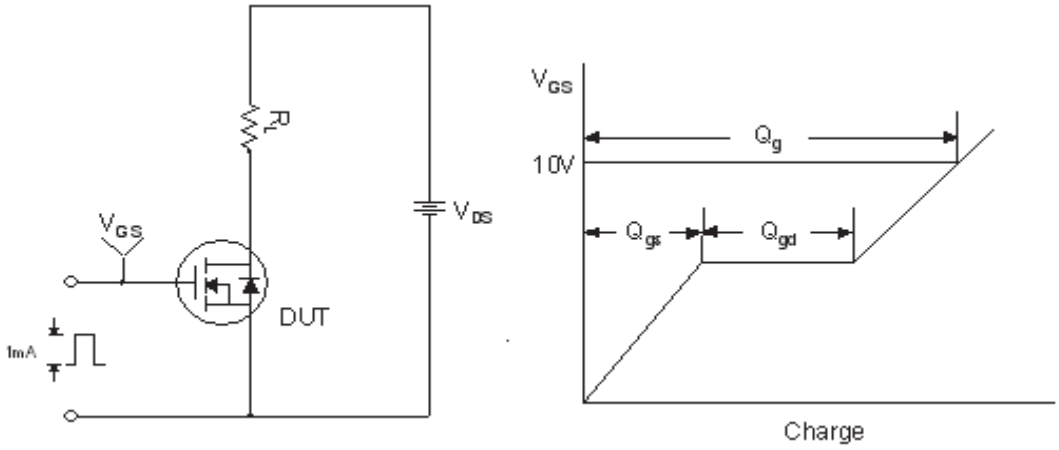


Figure 12. Gate Charge Test Circuit & Waveform

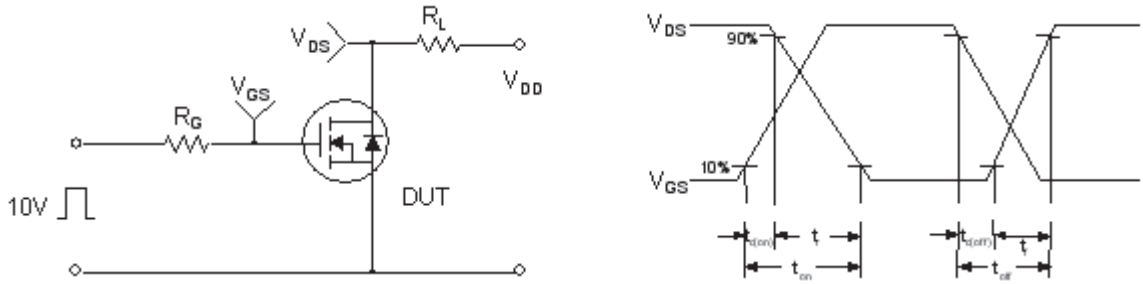


Figure 13. Resistive Switching Test Circuit & Waveforms

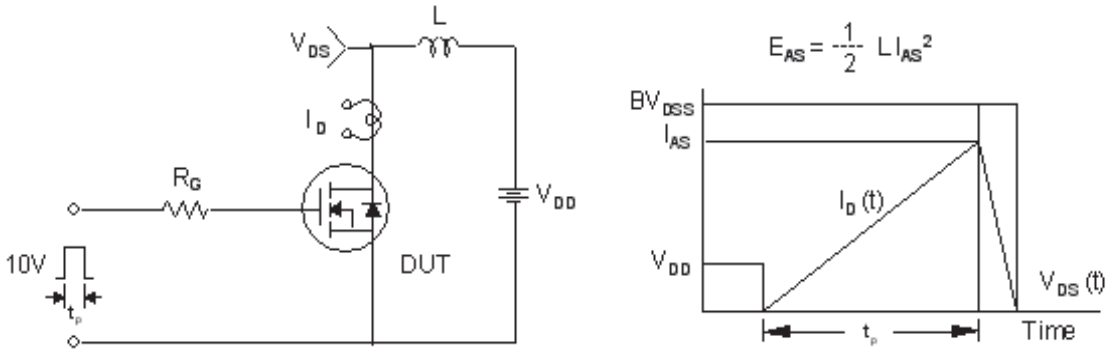


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

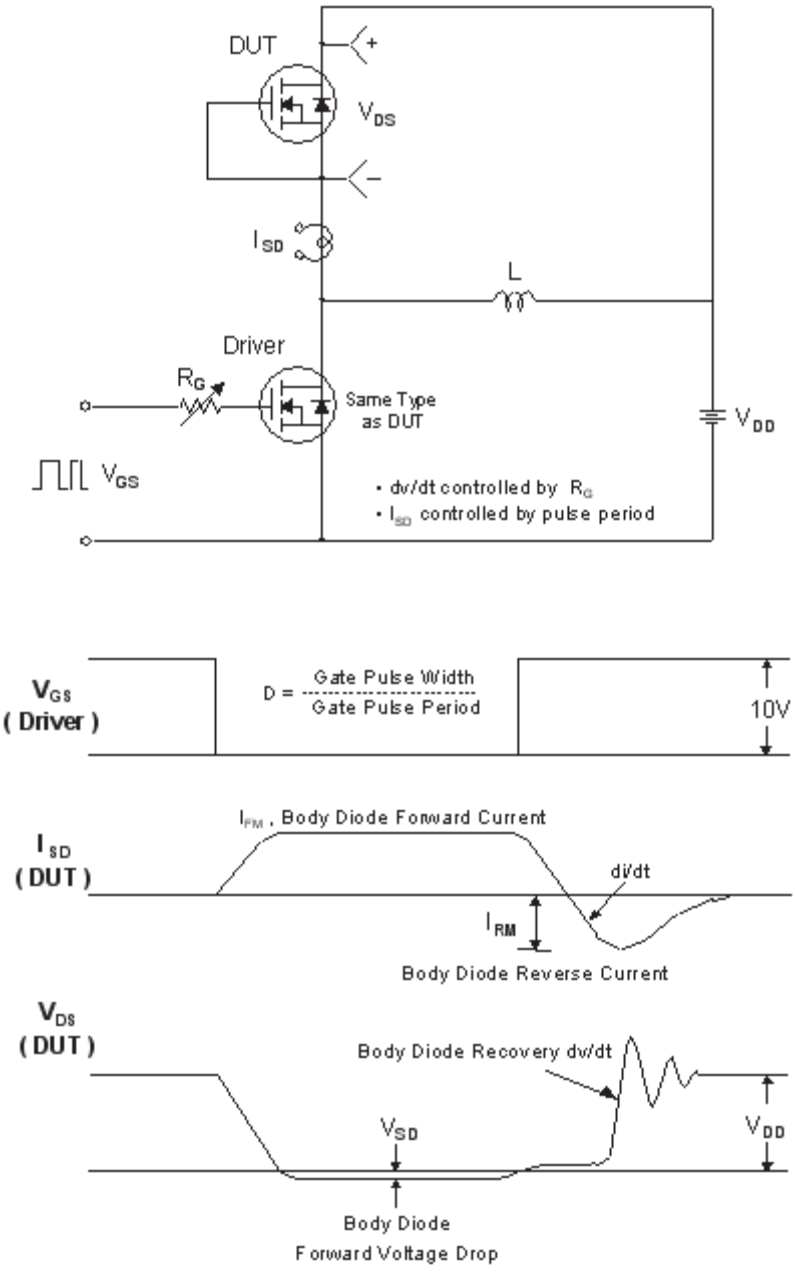


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

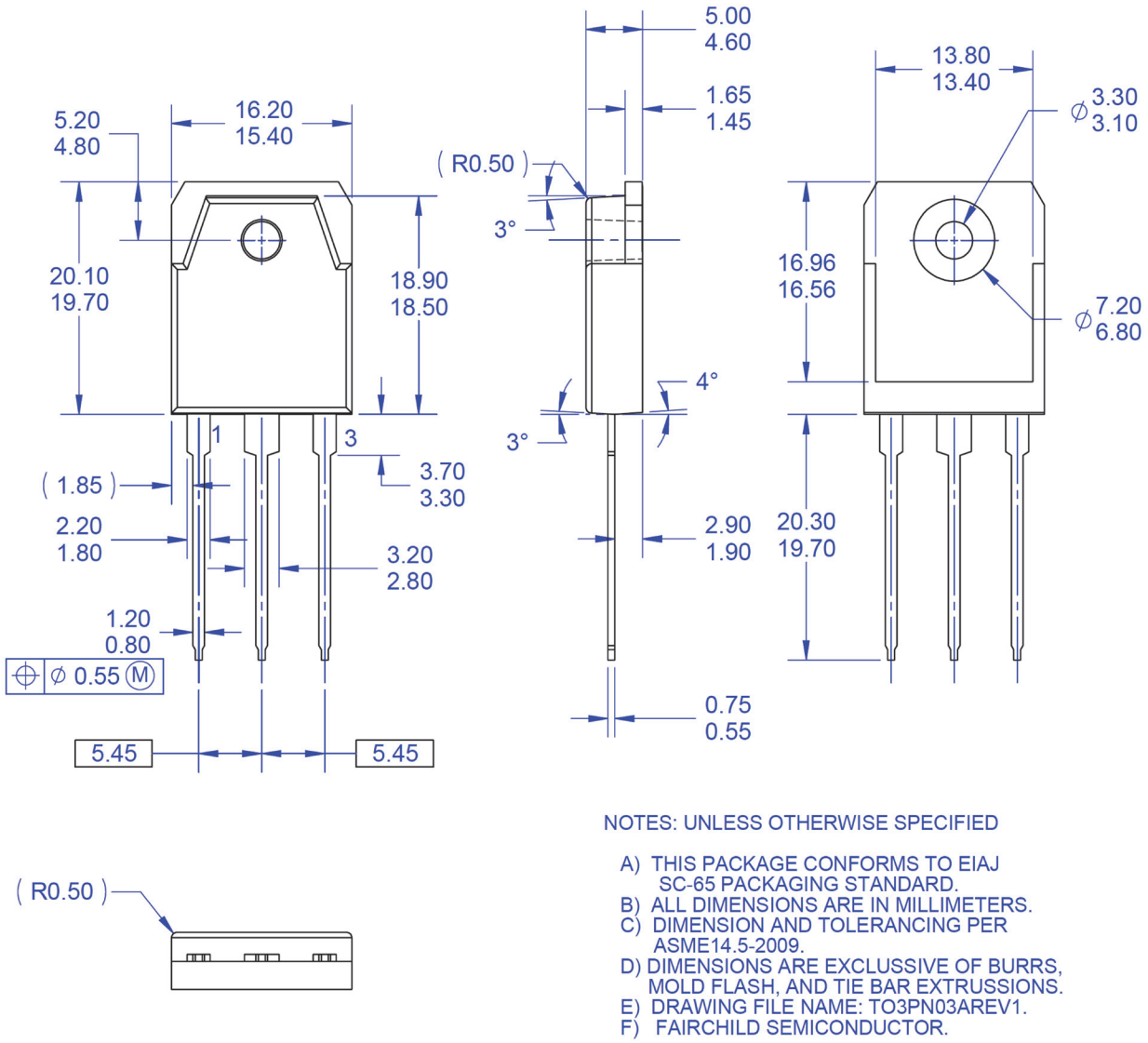


Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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